## Notice of References Cited Application/Control No. 10/647,534 Examiner Julio J. Maldonado Applicant(s)/Patent Under Reexamination DIP ET AL. Page 1 of 1

## U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	Α	US-2004/0121605 A1	06-2004	Maydan et al.	438/694
*	В	US-6,764,967 B1	07-2004	Pai et al.	438/787
*	С	US-6,613,677 B1	09-2003	Herbots et al.	438/694
*	D	US-6,589,877 B1	07-2003	Thakur, Randhir P.	438/703
*	Е	US-6,573,197 B2	06-2003	Callegari et al.	438/791
	F	US-			
	G	US-			
	Н	US-			
	ı	US-			
	,	US-			
	K	.US-			
	ا ا	US-			
	М	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
<u></u>	Q					
	R					
	s					
	T					

## **NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)			
	U .	Park et al., A study of modified silicon surface after CHF/sub3//Clsub2/Fsub6/ reactive ion etching, ETRI-Journal (south Korea Vol.16, no.1, pages 45-47, April 1994.			
	>	Wolf et al., Silicon Processing for the VLSI Era, Volume 1: Process Technology, 1986 by Lattice Press, pages 230-234, 568-574, 586-587 and 597-599.			
	w				
	x				

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.